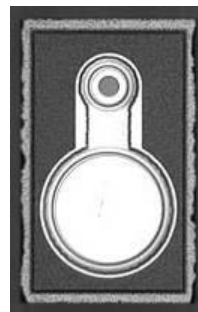




Features

- : 650 nm wavelength range
- : 25  $\mu\text{m}$  Emitting diameter
- : Other configurations available on request

Description



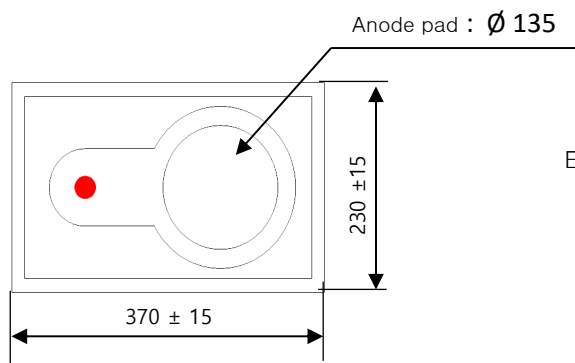
Applications

- : Sensors
- : Industrial applications

Absolute Maximum Ratings

| Parameter                  | Rating                  |
|----------------------------|-------------------------|
| Storage Temperature        | -40 to 100 °C           |
| Operating Temperature      | -20 to 70 °C            |
| Continuous Forward Current | 10mA                    |
| Continuous Reverse Voltage | 5V (@10 $\mu\text{A}$ ) |

Dimensions



Emission area :  $\text{Ø } 25$

Unit :  $\mu\text{m}$

Die Height :  $200 \pm 15 \mu\text{m}$



Electro-Optics Characteristics ( $T_a=25^\circ\text{C}$  unless otherwise stated)

| Parameters         | Symbol      | Specified |      |      | Unit | Test Conditions  |
|--------------------|-------------|-----------|------|------|------|------------------|
|                    |             | Min.      | Typ. | Max. |      |                  |
| Total Radiant Flux | $\Phi_o$    |           | 0.2  |      | mW   | $I_f=5\text{mA}$ |
| Peak Wavelength    | $\lambda_p$ | 640       | 650  | 665  | nm   | $I_f=5\text{mA}$ |
| Forward Voltage    | $V_f$       |           | 2.1  |      | nm   | $I_f=5\text{mA}$ |
| Reverse Current    | $I_R$       |           |      | 100  | nA   | $V_R=10\text{V}$ |

Test Data were measured in TO header of wire bonded chip

Value is referenced to the vender's measurement system (correlation to customer product is required).

Notes

\* These specifications are subject to change without notice.



NOTICE

The inherent design of this component causes it to be sensitive to electrostatic discharge(ESD). To prevent ESD-induced damage and/or degradation to equipment, take normal ESD precautions when handling this product